Perfluoroalkylpolyether Thin Layer–Induced Inhibition of Al_2O_3 Atomic Layer Deposition with a Trimethylaluminum Precursor

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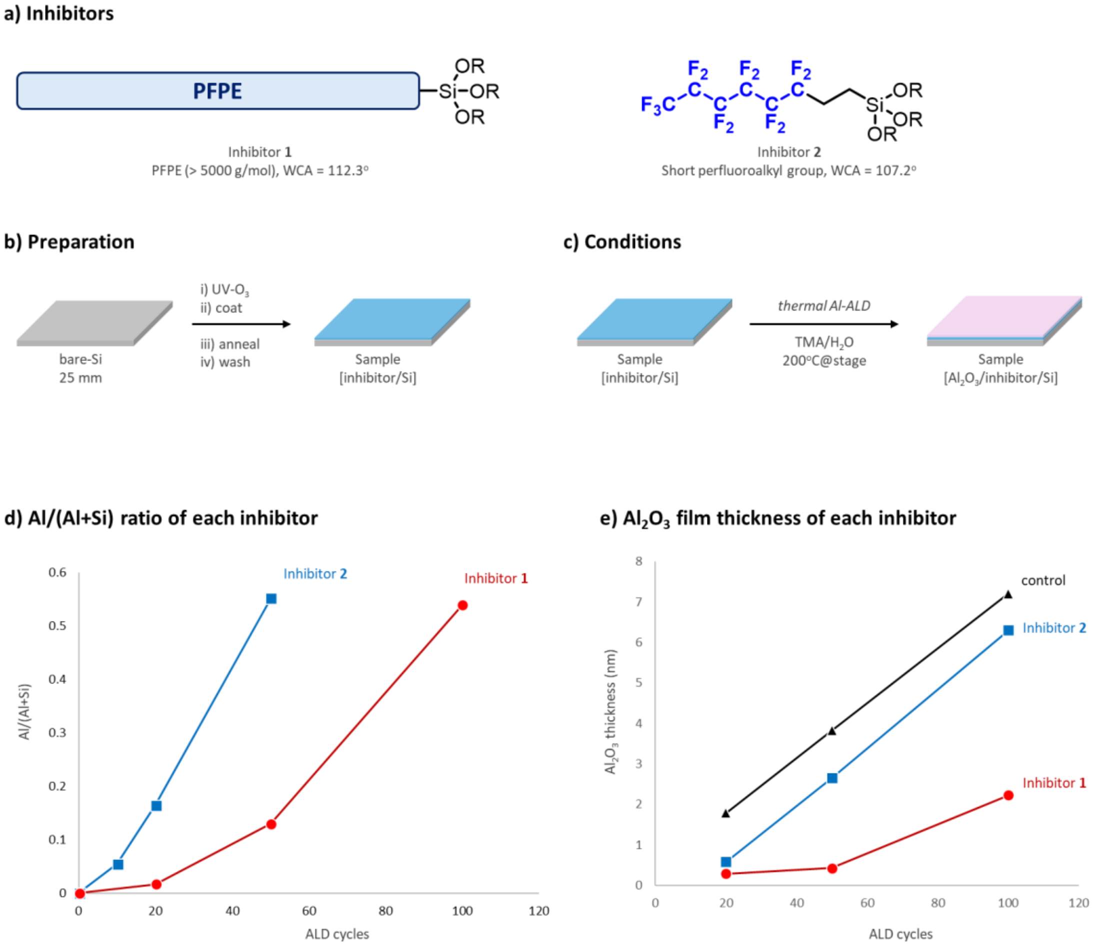
Supplemental Document

Figures



(a) Structures of inhibitors **1** and **2**. (b) Preparation method of inhibitor-coated samples. (c) ALD conditions employed in this presentation. (d) Al/(Al+Si) ratio of each sample obtained by XPS measurements. (e) Al_2O_3 film thickness of each sample obtained by ellipsometer.

References

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